



NCE N-Channel Super Trench Power MOSFET

Description

The NCEP6020AS uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

V_{DS} =60V,I_D =20A
R_{DS(ON)}=4.0mΩ (typical) @ V_{GS}=10V
R_{DS(ON)}=4.6mΩ (typical) @ V_{GS}=4.5V

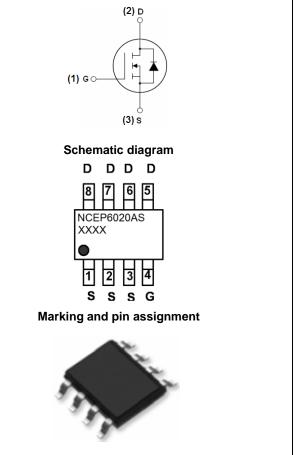
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

Package Marking and Ordering Information



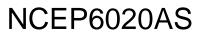
SOP-8 top view

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP6020AS	NCEP6020AS	SOP-8	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	60	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	Ι _D	20	А	
Drain Current-Continuous(Tc=100°C)	I _D (100℃)	14	А	
Pulsed Drain Current	I _{DM}	130	А	
Maximum Power Dissipation	PD	3.5	W	
Single pulse avalanche energy (Note 5)	E _{AS}	320	mJ	
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	°C	
Thermal Characteristic				
Thermal Resistance, Junction-to-Ambient ^(Note 2)	R _{θJA}	36	°C/W	





Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.7	2.4	V
		V_{GS} =10V, I_D =20A	-	4.0	4.5	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =18A	-	4.6	5.4	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =20A	35	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	N 00)()/ 0)/	-	4000	-	PF
Output Capacitance	C _{oss}	$V_{DS}=30V, V_{GS}=0V,$	-	680	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	23	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	11	-	nS
Turn-on Rise Time	tr	V_{DD} =30V, R _L =1.7 Ω	-	5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =3 Ω	-	56	-	nS
Turn-Off Fall Time	tf		-	12	-	nS
Total Gate Charge	Qg	<u>)// 00)/// 001</u>	-	67	-	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=30V, I_{D}=20A,$	-	12	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	8.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	20	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C, I_F = I_S$	-	48	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	60	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t \leq 10 sec.

3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25 $^\circ\!\mathrm{C}, V_{DD}{=}50V, V_{G}{=}10V, L{=}0.5mH, Rg{=}25\Omega$

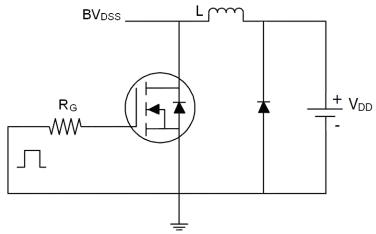


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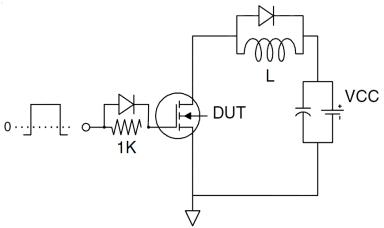
Pb Free Product



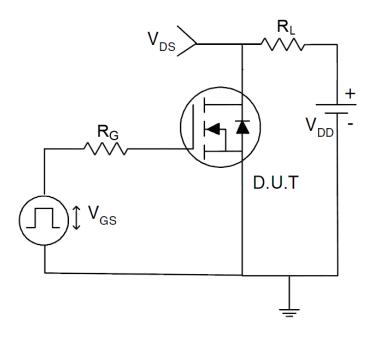
Test Circuit 1) E_{AS} test Circuit



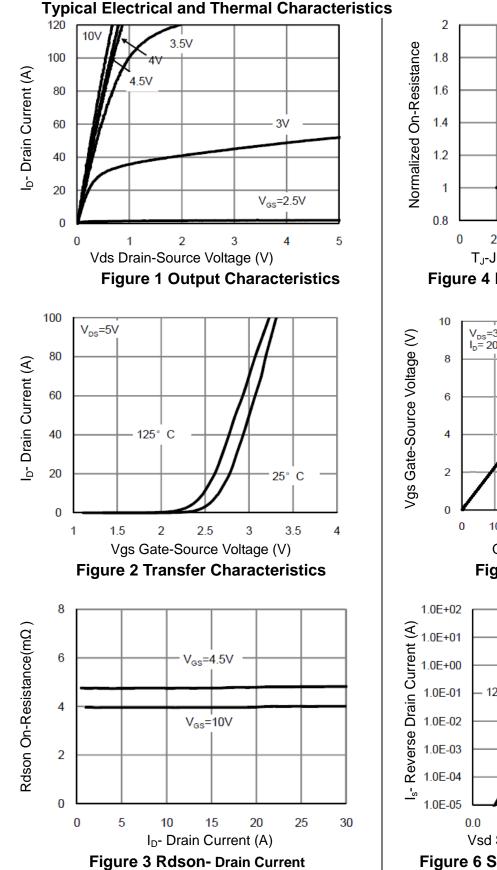
2) Gate charge test Circuit

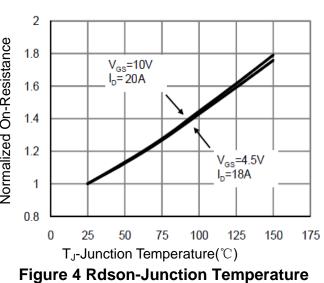


3) Switch Time Test Circuit



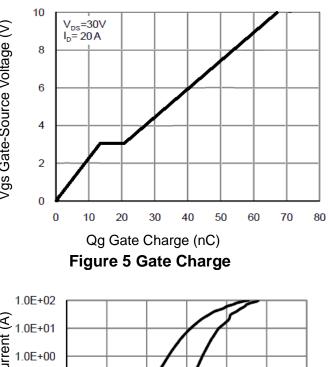


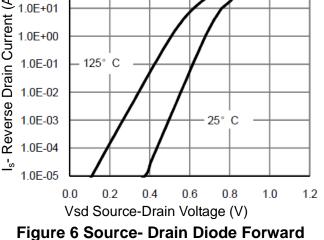




Pb Free Product

NCEP6020AS

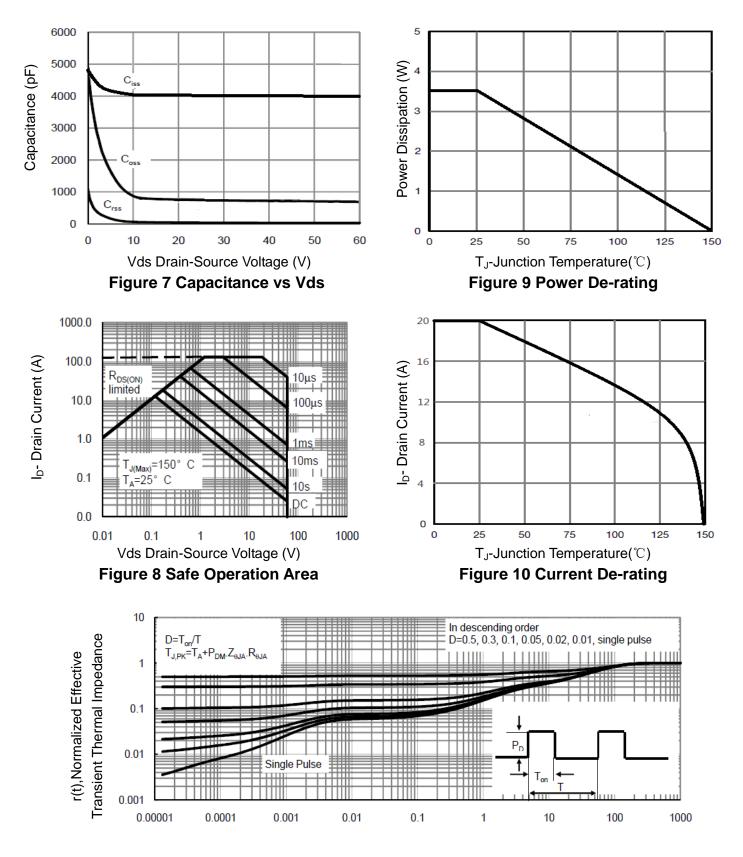






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Square Wave Pluse Duration(sec)

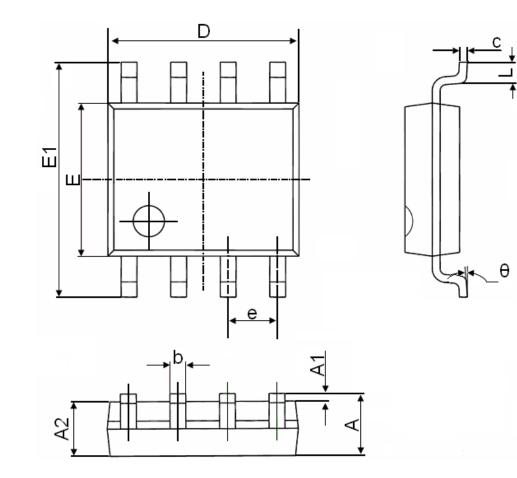
Figure 11 Normalized Maximum Transient Thermal Impedance



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SOP-8 Package Information



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
с	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
e	1.270(BSC)		0.050(BSC)		
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	





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